

Title (en)

SIC SEMICONDUCTOR SUBSTRATE, AND, PRODUCTION METHOD THEREFOR AND PRODUCTION DEVICE THEREFOR

Title (de)

SIC-HALBLEITERSUBSTRAT UND HERSTELLUNGSVERFAHREN DAFÜR UND HERSTELLUNGSVORRICHTUNG DAFÜR

Title (fr)

SUBSTRAT SEMI-CONDUCTEUR EN SIC ET PROCÉDÉ DE PRODUCTION S'Y RAPPORTANT ET DISPOSITIF DE PRODUCTION S'Y RAPPORTANT

Publication

**EP 3879010 A4 20220713 (EN)**

Application

**EP 19881264 A 20191105**

Priority

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- JP 2019043204 W 20191105

Abstract (en)

[origin: EP3879010A1] The problem to be addressed by the invention is to provide an SiC semiconductor substrate having a growth layer for which the step height has been controlled, a production method therefor, and a production device therefor. The invention is characterized by containing a growth step for causing an SiC substrate 10 to grow under an SiC-Si equilibrium vapor pressure environment. Causing the SiC substrate 10 to grow under the SiC-Si equilibrium vapor pressure environment in this manner allows the SiC semiconductor substrate for which the growth layer step height has been controlled, to be provided.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

- [X] US 2006144324 A1 20060706 - SAKAGUCHI YASUYUKI [JP], et al
- [X] WO 2017188381 A1 20171102 - KWANSEI GAKUIN EDUCATIONAL FOUND [JP]
- [X] WO 2017188382 A1 20171102 - KWANSEI GAKUIN EDUCATIONAL FOUND [JP]
- See also references of WO 2020095873A1

Designated contracting state (EPC)

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DOCDB simple family (publication)

**EP 3879010 A1 20210915**; **EP 3879010 A4 20220713**; CN 113227466 A 20210806; JP 7464806 B2 20240410; JP WO2020095873 A1 20211007; TW 202035807 A 20201001; US 2021399095 A1 20211223; WO 2020095873 A1 20200514

DOCDB simple family (application)

**EP 19881264 A 20191105**; CN 201980072707 A 20191105; JP 2019043204 W 20191105; JP 2020556060 A 20191105; TW 108140074 A 20191105; US 201917291572 A 20191105